



SANYO Semiconductors

DATA SHEET

2SK2534

N-Channel Silicon MOSFET

General-Purpose Switching Device Applications

Features

- Low ON-resistance.
- High-speed switching.
- Enables simplified fabrication, high-density mounding, and miniaturization in end products due to the surface mountable package.

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V _{DSS}		250	V
Gate-to-Source Voltage	V _{GSS}		±30	V
Drain Current (DC)	I _D		16	A
Drain Current (Pulse)	I _{DP}	PW≤10μs, duty cycle≤1%	64	A
Allowable Power Dissipation	P _D	Tc=25°C	50	W
Channel Temperature	T _{ch}		150	°C
Storage Temperature	T _{stg}		-55 to +150	°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	V _{(BR)DSS}	I _D =1mA, V _{GS} =0V	250			V
Gate-to-Source Breakdown Voltage	V _{(BR)GSS}	I _G = ±100μA, V _{DS} =0V	±30			V
Zero-Gate Voltage Drain Current	I _{DSS}	V _{DS} =250V, V _{GS} =0V			1.0	mA
Gate-to-Source Leakage Current	I _{GSS}	V _{GS} = ±25V, V _{DS} =0V			±10	μA
Cutoff Voltage	V _{GS(off)}	V _{DS} =10V, I _D =1mA	2.0		3.0	V
Forward Transfer Admittance	y _{fs}	V _{DS} =10V, I _D =8A	8.5	14		S

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2SK2534

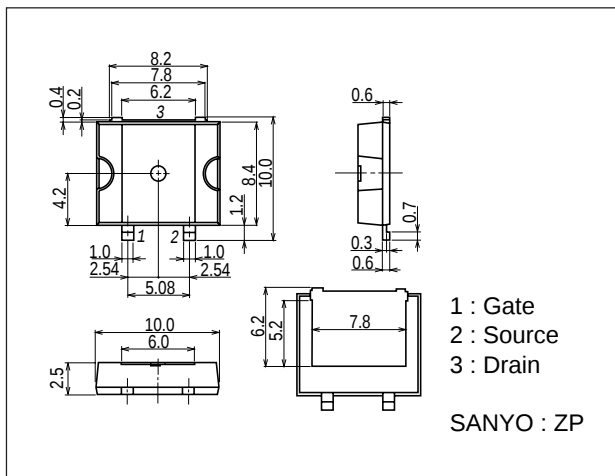
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Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Static Drain-to-Source On-State Resistance	$R_{DS(on)}$	$I_D=8A$, $V_{GS}=10V$		130	180	$m\Omega$
Input Capacitance	C_{iss}	$V_{DS}=20V$, $f=1MHz$		1950		pF
Output Capacitance	C_{oss}	$V_{DS}=20V$, $f=1MHz$		455		pF
Reverse Transfer Capacitance	C_{rss}	$V_{DS}=20V$, $f=1MHz$		185		pF
Turn-ON Delay Time	$t_{d(on)}$	See specified Test Circuit.		28		ns
Rise Time	t_r	See specified Test Circuit.		96		ns
Turn-OFF Delay Time	$t_{d(off)}$	See specified Test Circuit.		500		ns
Fall Time	t_f	See specified Test Circuit.		150		ns
Diode Forward Voltage	V_{SD}	$I_S=16A$, $V_{GS}=0V$		1.0	1.5	V
Diode Reverse Recovery Time	t_{rr}	$I_S=16A$, $di/dt=100A/\mu s$		180		ns

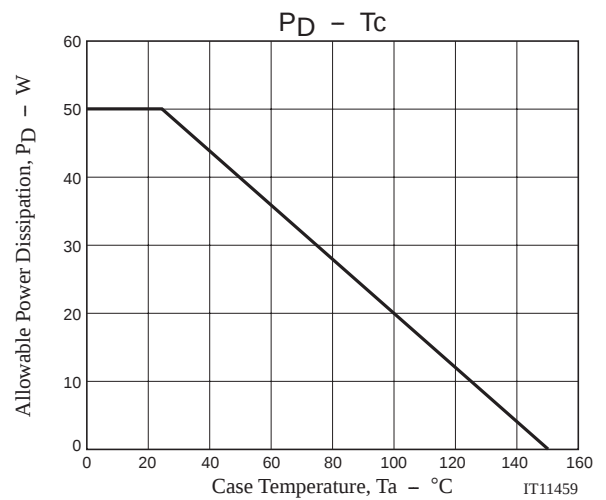
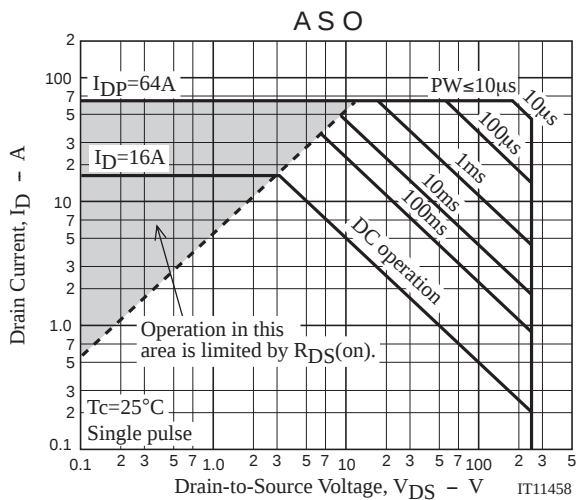
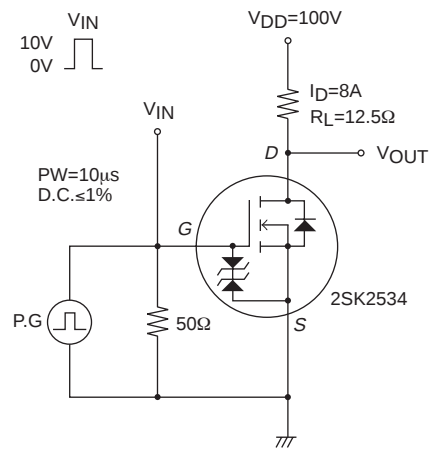
Package Dimensions

unit : mm (typ)

7002-001



Switching Time Test Circuit



Note on usage : Since the 2SK2534 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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